

## Single Phase Rectifier Bridge

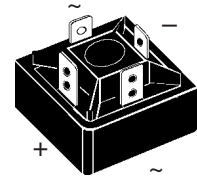
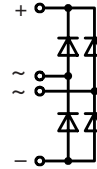
Standard and Avalanche Types

$$I_{dAV} = 18 \text{ A}$$

$$V_{RRM} = 800-1600 \text{ V}$$

| $V_{RSM}$<br>V | $V_{BRmin}$ ①<br>V | $V_{RRM}$<br>V | Standard<br>Types | Avalanche<br>Types |
|----------------|--------------------|----------------|-------------------|--------------------|
| 900            |                    | 800            | VBO 13-08NO2      |                    |
| 1300           | 1230               | 1200           | VBO 13-12NO2      | VBO 13-12AO2       |
| 1500           | 1430               | 1400           | VBO 13-14NO2      | VBO 13-14AO2       |
| 1700           | 1630               | 1600           | VBO 13-16NO2      | VBO 13-16AO2       |

① For Avalanche Types only



| Symbol      | Conditions  | Maximum Ratings             | Features  |                      |
|-------------|---|-----------------------------|---|----------------------|
| $I_{dAV}$ ② | $T_C = 85^\circ\text{C}$ , module                               | 18 A                        | <ul style="list-style-type: none"> <li>Avalanche rated parts available</li> <li>Package with DCB ceramic base plate</li> <li>Isolation voltage 3600 V~</li> <li>Planar passivated chips</li> <li>Low forward voltage drop</li> <li>1/4" fast-on terminals</li> <li>UL registered E 72873</li> </ul> |                      |
| $I_{dAVM}$  | module  | 30 A                        |   |                      |
| $P_{RSM}$   | $T_{VJ} = T_{VJM}$ t = 10 $\mu\text{s}$                         | 2.5 kW                      |   |                      |
| $I_{FSM}$   | $T_{VJ} = 45^\circ\text{C}$ ;<br>$V_R = 0$                      | t = 10 ms (50 Hz), sine     |   | 220 A                |
|             |   | t = 8.3 ms (60 Hz), sine    |   | 230 A                |
| $I^2t$      | $T_{VJ} = 45^\circ\text{C}$ ;<br>$V_R = 0$                      | t = 10 ms (50 Hz), sine     |   | 180 A                |
|             |   | t = 8.3 ms (60 Hz), sine    |   | 190 A                |
| $I^2t$      | $T_{VJ} = T_{VJM}$ ;<br>$V_R = 0$                               | t = 10 ms (50 Hz), sine     |   | 240 A <sup>2</sup> s |
|             |   | t = 8.3 ms (60 Hz), sine    |   | 220 A <sup>2</sup> s |
| $T_{VJ}$    |   | -40...+150 $^\circ\text{C}$ |   |                      |
| $T_{VJM}$   |   | 150 $^\circ\text{C}$        |   |                      |
| $T_{stg}$   |   | -40...+125 $^\circ\text{C}$ |   |                      |
| $V_{ISOL}$  | 50/60 Hz, RMS t = 1 min<br>$I_{ISOL} \leq 1 \text{ mA}$ t = 1 s | 3000 V~                     |   |                      |
|             |   | 3600 V~                     |   |                      |
| $M_d$       | Mounting torque (M5)<br>(10-32 UNF)                             | 1.5-2 Nm<br>13-18 lb.in.    |   |                      |
| Weight      | typ.  | 15 g                        |   |                      |

### Features

- Avalanche rated parts available
- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Low forward voltage drop
- 1/4" fast-on terminals
- UL registered E 72873

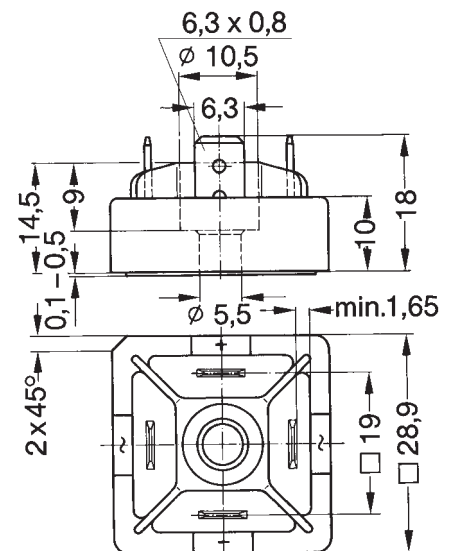
### Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

### Advantages

- Easy to mount with one screw
- Space and weight savings
- Improved temperature and power cycling

### Dimensions in mm (1 mm = 0.0394")



| Symbol     | Test Conditions                                       | Characteristic Values |
|------------|---|-----------------------|
| $I_R$      | $V_R = V_{RRM}$ ;<br>$T_{VJ} = 25^\circ\text{C}$      | $\leq 0.3 \text{ mA}$ |
|            | $V_R = V_{RRM}$ ;<br>$T_{VJ} = T_{VJM}$               | $\leq 5 \text{ mA}$   |
| $V_F$      | $I_F = 55 \text{ A}$ ;<br>$T_{VJ} = 25^\circ\text{C}$ | $\leq 1.8 \text{ V}$  |
| $V_{T0}$   | For power-loss calculations only                      | 0.85 V                |
| $r_T$      | $T_{VJ} = T_{VJM}$                                    | 17 m $\Omega$         |
| $R_{thJC}$ | per diode; DC current                                 | 5.6 K/W               |
|            | per module  | 1.4 K/W               |
| $R_{thJK}$ | per diode; DC current                                 | 6.0 K/W               |
|            | per module  | 1.5 K/W               |
| $d_s$      | Creeping distance on surface                          | 13 mm                 |
| $d_A$      | Creepage distance in air ③                            | 9.5 mm                |
| $a$        | Max. allowable acceleration                           | 50 m/s <sup>2</sup>   |

Data according to IEC 60747 and refer to a single diode unless otherwise stated  
 ② for resistive load at bridge output, ③ with isolated fast-on tabs.

IXYS reserves the right to change limits, test conditions and dimensions.

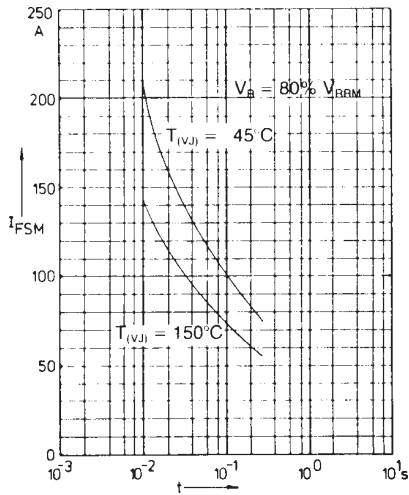


Fig. 1 Surge overload current per diode  
 $I_{FSM}$ : Crest value,  $t$ : duration

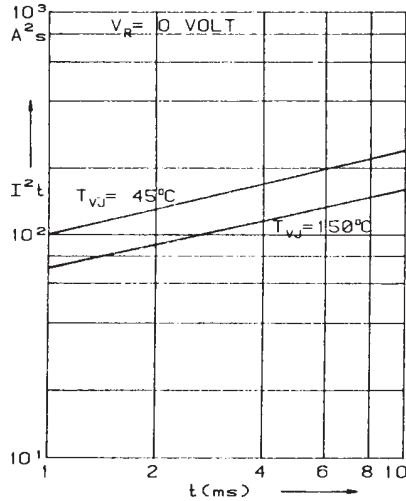


Fig. 2  $I^2t$  versus time (1-10 ms) per diode

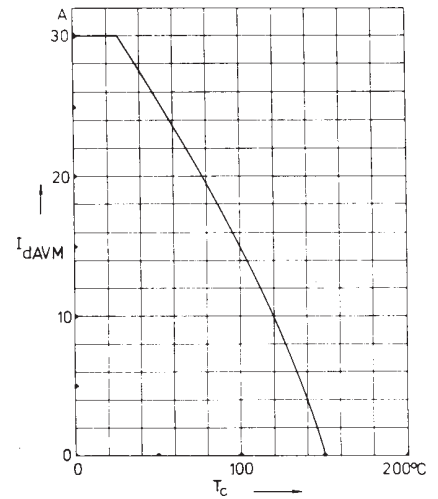


Fig. 3 Max. forward current at case temperature

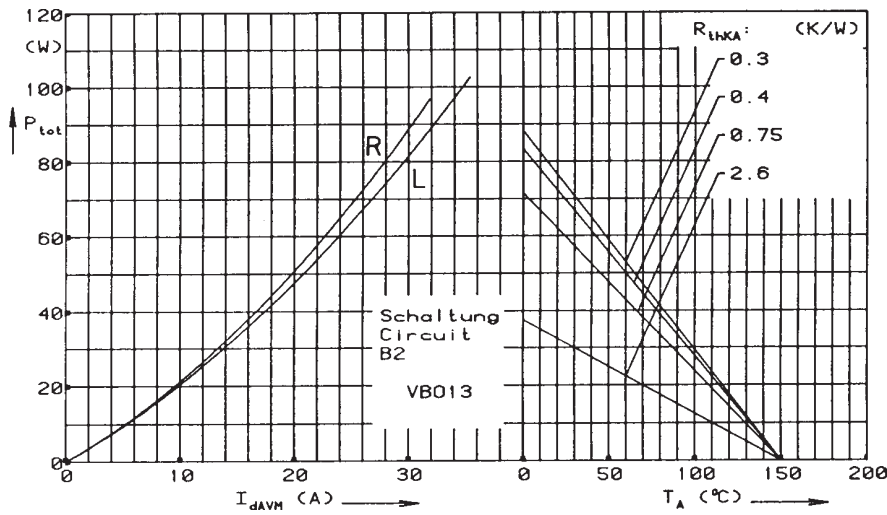


Fig. 4 Power dissipation versus direct output current and ambient temperature

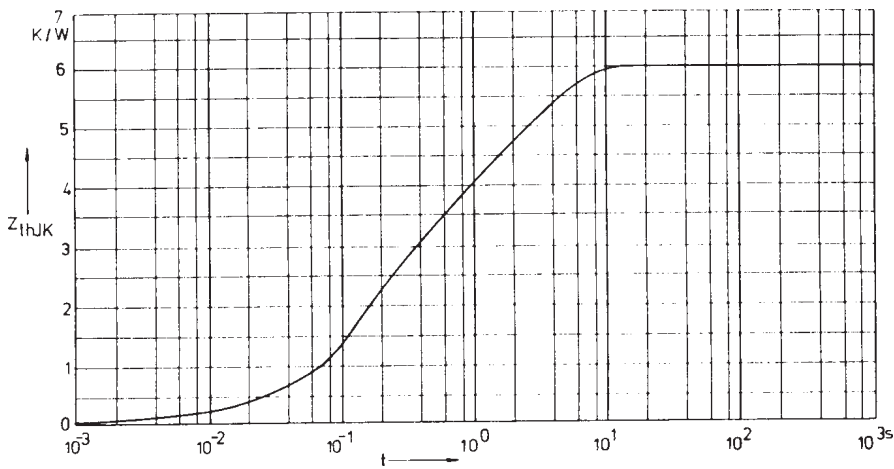


Fig. 5 Transient thermal impedance junction to heatsink per diode

Constants for  $Z_{thJK}$  calculation:

| i | $R_{thi}$ (K/W) | $t_i$ (s) |
|---|-----------------|-----------|
| 1 | 0.059           | 0.00217   |
| 2 | 2.714           | 0.159     |
| 3 | 3.227           | 2.34      |